Integration of external electric fields in molecular dynamics simulation models for resistive switching devices

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Resistive switching devices emerged a huge amount of interest as promising candidates for non-volatile memories as well as artificial synapses due to their memristive behaviour. The main physical and chemical phenomena which define their functionality are driven by externally applied voltages, and the resulting electric fields. Although molecular dynamics simulations are widely used in order to describe the dynamics on the corresponding atomic length and time scales, there is a lack of models which allow for the actual driving force of the dynamics, i.e. externally applied electric fields. In this work, we propose such a model, which can be applied particularly to describe the for resistive switching devices preferred metal-isolator-metal systems. It has been shown that the calculated electric field and force distribution in case of the chosen example system Cu/a-SiO$_2$/Cu are in agreement with fundamental field theoretical expectations.

I. INTRODUCTION

Physical neural networks are typically investigated to utilize the efficiency of the biological information processing. The function of the neural synapses are emulated by resistive switching devices. Of paramount importance in this and the context of non-volatile memories is their memristive behaviour [1,2]. Many of these two terminal devices have a conceptually simple metal-insulator-metal structure and rely on ionic mechanisms on the nanometer length scale, one of which is electrochemical metallization indicated in Fig [1]. (I) oxidation of metal atoms at the active electrode, (II) drift of the resultant ions within the dielectric and (III) reduction at the opposite electrode. Resistive switching is a consequence of the formation and re-formation of conductive metal filaments inside the insulator. It has been shown, that the processes on the device length scale and on the experimental time scale, i.e. microseconds to minutes can be successfully simulated by means of kinetic Monte Carlo (KMC) methods [3,4]. However, KMC simulations rely inherently on the identification of all important physical and chemical processes and their corresponding transition rates. These informations are crucial for reliably modelling the device dynamics and can be gathered to a great extent by classical molecular dynamics (CMD) simulations.

Within CMD approaches Newton’s equations of motion are solved subject to interaction potentials, which resemble the respective quantum mechanical behaviour. Therefore, the CMD method provides the basis for a deeper understanding of the physical processes on atomic time scales [5]. It is however important to note that the dynamics of resistive switching devices and their functionality are mainly driven by externally applied voltages and therefore externally applied electric fields. Up to know, only a a small number of CMD models which allow for externally applied electric fields and reactive systems have been reported [6-9]. Despite the excellent performance of these models in their respective case they are not suitable for the simulation of arbitrary metal-insulator-metal systems. This is due to the common restrictions of the thicknesses of the insulating material in the order of 10 Å and the assumption of a non-ideal insulator. The former is caused by the potential cutoff radius generated interaction limitations. The latter can be caused by global polarization charge transfer currents between atoms, which will be discussed later in greater detail. In order to overcome these limitations and remedy the lack of a generic model, we propose an alternative scheme for electric fields in self-consistent CMD simulations of metal-insulator-metal systems. The model is based on the separated treatment of the different kinds of electric forces in field driven metal-insulator-metal systems. Thereby, the fluctuating charge model QTPIE (charge transfer polarization current equalization) has been chosen to describe the polarization of the insulator [10-12]. Overall, the proposed model is compatible with any charge equilibration based CMD potential and the widely used molecular dynamics simulation tool LAMMPS [13].

The model has been validated by using the reactive force field (ReaxFF) to simulate a Cu/a-SiO$_2$/Cu material stack as an example system. We have chosen this particular system as Cu/a-SiO$_2$ is an often used electrode/insulator material composition for electrochemical metallization memristive devices [14]. ReaxFF itself is based on bond-order dependent interactions, whereas the respective parameter sets are fitted to experimental findings and ab initio calculations [15].

In our model, electrostatic forces are described by means of modified Coulomb interactions of atomic point charges. The fluctuating and environment dependent charge distribution is calculated self-consistently with the QTPIE method. Ultimately, it has been shown, that
FIG. 1. Cu/a-SiO$_2$/Cu electrochemical metalization cell with the fundamental processes of oxidation (I), drift (II), and reduction of Cu-atoms/-ions (III).

the proposed integration for the electric field is particularly applicable to investigate resistive switching in electrochemical metalization cells due to the dependency of the respective fundamental processes on the electric field. Due its generic character, the model can be easily utilized for any field driven metal-conductor-metal or metal-insulator-metal system.

II. ELECTRIC FIELD AND FORCE MODEL

In metal-insulator-metal resistive switching devices the most important physical and chemical processes are driven by external electric fields. The related electric forces which act on interfacial metal atoms can be split into three parts, which will be discussed below. For this ansatz the electric field at the position of the $i$-th atom is decomposed into two parts, i.e., $E_{\text{ext},i}$ and $E_{\text{int},i}$. The latter is given as $E_{\text{int},i} = E_{\text{dep},i} + E_{0,i}$. $E_{0,i}$ describes Coulomb interactions without any externally applied voltage and $E_{\text{dep},i}$ describes the depolarization field.

First, the forces acting on the free charges at the electrodes as a result of the applied voltage are expressed by means of the Maxwell stress tensor $T(E_{\text{int}},E_{\text{ext}})_i$ and $T(E_{\text{ext}})_i$ as a function of the respective electric fields

$$F_{\text{free},i} = \int_V \rho_{\text{free}} E_i d^3 r,$$

(1)

$$= \int_{\partial V} \epsilon_0 [T(E_{\text{ext}})_i + T(E_{\text{int}}, E_{\text{ext}})_i] \cdot n d f. \quad (2)$$

However, this term is zero for any atom inside the insulator. Second, the electric forces due to the external electric field acting on the polarization charge distribution are described by $q_{\text{pol},i}E_{\text{ext},i}$. The polarized charge of the $i$-th atom is given here by $q_{\text{pol},i}$. Third, the Coulomb forces on these charges are described by $q_{\text{pol},i}E_{\text{int},i}$.

Altogether the electric forces on interfacial metal atoms can be expressed as

$$F_i = \int_{\partial V} \epsilon_0 [T(E_{\text{ext}})_i + T(E_{\text{int}}, E_{\text{ext}})_i] \cdot n d f \ldots$$

$$\ldots + q_{\text{pol},i}E_{\text{ext},i} + q_{\text{pol},i}E_{\text{int},i}. \quad (3)$$

The subsequent calculation of the forces acting on the $i$-th atom can be divided into three complementary parts: i) The calculation of the external electric potential $\Phi_{\text{ext}}$ and field $E_{\text{ext}}$, ii) the calculation of the polarized charges $q_{\text{pol}}$, and the internal electric field $E_{\text{int}}$, and iii) the calculation of the Maxwell stress tensor $T(E_{\text{int}}, E_{\text{ext}})$ and $T(E_{\text{ext}})$. In the following sections, these three parts are separately discussed.

A. Calculation of the external electric field

The calculation of the potential $\Phi_{\text{ext}}$ due to the externally applied voltage is based on solving the Laplace equation,

$$\nabla^2 \Phi_{\text{ext}} = 0, \quad (4)$$

subject to appropriate boundary conditions. The application of Dirichlet boundary conditions requires a continuous representation. Therefore, the interfaces are interpolated. The electric field can then be calculated on grid points by

$$E_{\text{ext}} = -\nabla \Phi_{\text{ext}}. \quad (5)$$

This is appropriate since the electrostatic approximation of Maxwell’s equation is justified.

B. Calculation of the polarized charges and of the internal electric field

The externally applied electric field influences the overall atomic charge distribution. Therefore, a model for the fluctuating charges is needed. In the widely used charge equilibration (QEq) method, the energy of the system is expanded in the charge distribution and truncated after the second order. The first- and second-order terms are identified with the electronegativity and the hardness, respectively. The equalization of the electronegativity or the chemical potential by charge transfer within the bonded system leads to the charge distribution, which minimizes the electrostatic energy under the constraint of charge neutrality. The corresponding system of linear equations can be solved by applying the method of Lagrange multiplier [16,17]. This formalism implies global charge transfer currents between the atoms, where distances represent no limitations. Nevertheless, this method provides in general a satisfactory description for many cases without any external perturbation. The response to an external electric field is though always a global rearrangement of the atomic charges, comparable to an ideal conductor. As a consequence with this
method the polarization of insulators is only modelled insufficiently and the net electric field inside the insulator is zero \[9\].

Since in the present case the electrodes are typically separated by a thin insulator, an effective and efficient model for fluctuating charges is needed. Therefore, the QEeq method is extended to the charge transfer polarization current equalization (QTPIE) method, where polarization currents between atoms are locally limited \[10\].

The formalism itself is similar to the formalism of the QEeq method, whereas the atomic charge variables \(q_i\) are initially substituted with the corresponding sum of charge transfer variables \(p_{ij}\), which describe the charge transfer from atom \(j\) to atom \(i\). The application of charge transfer variables is meanwhile similar to the SQE approach \[18\]. However, in this work an additional term for long-range charge transfer currents between the atoms has been included. The subsequent expression for the electrostatic energy as a function of the atomic charge variables, \(q_i = \sum_j p_{ji}\) \[11\]. The resultant equation for the electrostatic energy is then given by

\[
W_{es} = \sum_i \chi_{eff,i} q_i \left(1 + \frac{1}{2} \sum_j J_{ij}^2 \right) + \frac{1}{4\pi\epsilon_0} \sum_{ij} \text{Tap}(r_{ij}) \frac{q_i q_j}{(r_{ij}^3 + \gamma_{ij}^3)^{-3}}.
\]

This equation resembles the initial expansion of the energy in the charge distribution, whereas for simplicity the charge independent term is omitted. The tapering function \(\text{Tap}(r_{ij})\) is used to avoid cutoff radius generated discontinuities within the potential energy surface. In addition the \(\gamma_{ij}\) value is introduced in order to allow for screening effects. The first term corresponds with the first-order of the beforehand mentioned expansion and is responsible for the spatial limitations of the charge transfer between atoms by the definition of the effective electronegativity

\[
\chi_{eff,i,0} = \frac{\sum_j (\chi_i - \chi_j) S_{ij}}{\sum_{j'} S_{ij'}}.
\]

This atomic property is computed by weighting the differences of an atom and its surrounding atoms’ electronegativities with the corresponding overlap integral of Gaussian-type orbitals (GTOs) \(S_{ij}\). The latter has been chosen in favor of Slater-type orbitals due to its simpler computation \[10\].

In case of electric fields, the change in the electrostatic energy is taken into account by the following modification of the effective electronegativity

\[
\chi_{eff,i} = \frac{\sum_j (\chi_i - \chi_j + \Phi_j) S_{ij}}{\sum_{j'} S_{ij'}} - \Phi_i.
\]

This is a slightly modified version compared with the model presented by Chen et al. The detailed derivation of the energy and the effective electronegativities can be found in \[12\]. Since this ansatz leads on one hand to the polarization inside the dielectric and on the other hand to a corresponding compensation at the electrodes, this kind of polarization model is well suited for the investigation of voltage driven memristive devices.

The second and the third term of \[9\] describe the second-order corrections of the energy expansion, whereas the Coulomb self-energy and Coulomb interactions are treated separately. The equation for the latter originates from the electron equilibration method and is also used for the ReaxFF potential \[20\], \[21\]. Subsequently the electric field can be directly calculated from the latter contribution to the electrostatic energy,

\[
E_{int} = -\sum_{ij} \frac{1}{4\pi\epsilon_0} \nabla \left( \text{Tap}(r_{ij}) \frac{q_i q_j}{(r_{ij}^3 + \gamma_{ij}^3)^{-3}} \right).
\]

### C. Calculation of the Maxwell stress tensor

If both the external and internal electric fields are known, the components of the Maxwell stress tensors can be calculated by

\[
T_{mn}(E_{ext}) = E_{ext,m} E_{ext,n} - \frac{E_{ext,m} E_{ext,n}}{2} \delta_{mn}, \quad (10)
\]

\[
T_{mn}(E_{int}, E_{ext}) = E_{int,m} E_{ext,n} \ldots - \frac{E_{int,m} E_{ext,n}}{2} \delta_{mn}, \quad (11)
\]

using the Einstein’s summation convention with the Dirac delta function \(\delta_{mn}\).

### III. Validation of the Model

To validate the developed model, the electric field and force distribution is calculated within an exemplary Cu/a-SiO\(_2\)/Cu system. Dirichlet boundary conditions have been applied in \(z\) direction, whereas in \(x\) and \(y\) direction periodic boundary conditions have been chosen (see Fig. \[2\]). For all performed simulations a suitable potential has been used within the chosen molecular dynamics simulation code LAMMPS. The actual field and force calculation model is consistently coupled with LAMMPS via a Python interface \[6\], \[13\], \[22\], \[23\]. At first, the preparation of the example system is described. Afterwards, a suitable diagnostic method to measure electric fields is developed. Finally, the validation results for our model are presented and discussed.

#### A. System preparation

The a-SiO\(_2\) layer has been prepared according to the procedure published by Fogarty et al. \[24\]. For this, the implemented versions of the Nosé-Hoover thermostat, the
The term $F_{0,i}$ is the force on an atom without any applied voltage. (13) is implemented by the inversion of the sign of the original effective electronegativities $\chi_{\text{eff},i}$. As a result, the external electric field $E_{\text{ext},i}$, depolarization field $E_{\text{dep},i}$, and their superposition $E_i$ can be measured within molecular dynamics simulations by a repeated force measuring time step,

$$E_{\text{ext},i} = \frac{F_i|_{\chi_{\text{eff},i}} - F_i|_{-\chi_{\text{eff},i}}}{2q_{\text{pol},i}},$$

$$E_{\text{dep},i} = \frac{F_i|_{\chi_{\text{eff},i}} + F_i|_{-\chi_{\text{eff},i}} - 2F_{0,i}}{2q_{\text{pol},i}},$$

$$E_i = \frac{F_i|_{\chi_{\text{eff},i}} - F_{0,i}}{q_{\text{pol},i}}.$$  

C. Results and Discussion

This section covers the results concerning validation and consistency of the proposed model for an arbitrarily chosen voltage of 4 V. Fig. 3 shows the projection of the $z$ component of the external electric field, depolarization field, and the superposition of both within the dielectric along the $z$ axis at the atom sites. The mean value of the external electric field within the dielectric fluctuates slightly around 0.08 V/Å, which is in agreement with approximate calculations for the electric field strength of a parallel plate capacitor. In the vicinity of the Cu electrodes the electric field follows the negative gradient of the potential and is therefore decreased until it completely vanishes inside the electrodes.

The calculated depolarization field fluctuates around...
FIG. 4. (a) Absolute value of the forces on the free charges of the top electrode and (b) interpolation of the metal atom positions. Interfacial electrode atoms are illustrated as circles. The surface elements are colored as a function of the force acting on the respective nearest atom. On the right hand side: Schematic of the chosen colors dependent on the interfacial atom positions.

$\Delta x$ (Å)

0 V/Å within the a-SiO$_2$ due to a local compensation. The negative field component in the vicinity of the electrodes originates from the net contribution of the polarization charges. Due to the case of constant potentials a corresponding field and net charge is expected at the electrodes. The minor fluctuations within the a-SiO$_2$ are caused by interactions on the atomic scale. Hence, the resulting electric field within the system matches the expectations well. At last the implementation of the forces on the free charges at the copper electrodes is verified. Fig. 4 (a) shows the resulting force distribution at the top electrode. Cu atoms are illustrated as circles. A consistent relation between the interface curvature and the force distribution is expected due to the utilization of the former as Dirichlet boundary condition in the computation of the latter. Fig. 4 (b) shows the relative displacement from the atoms’ mean z coordinate at the top electrode. The corresponding force distribution on the electrode matches again well with the expectations taking the curvature of the interface into account. The closer the interfacial atom site towards the opposite electrode the greater the received force. The opposite can be observed for the inverse case.

The calculated electric field and force distribution in case of the chosen example system Cu/a-SiO$_2$/Cu are in agreement with fundamental field theoretical expectations. This shows that the made approximations within the model and the diagnostics of the electric fields are correct.

For instance the depolarization field is modeled assuming a restriction of the polarization along interatomic bonds, whereas any perpendicular contribution is neglected [12]. In addition, the influence of atomic rearrangement is neglected within the measurement of the depolarization field. However, the validation shows that those effects are of minor importance in this case. Thus, for material systems where the contribution of those mechanisms to the polarization is significant the presented diagnostics should be used with care.

IV. CONCLUSIONS

A model of externally applied electric fields for molecular dynamics simulations and its fundamental implications to the atomic system for generic metal-insulator-metal systems has been proposed. The model remedies certain drawbacks of existing models, e.g., restrictions to conductive dielectrics and thicknesses of the insulating material in the order of 10 Å. The extension of applicable systems originates from the force separation into long range electric forces and local polarization effects. As a consequence limitations due to the potential cutoff radius are bypassed.

The model is applied to a resistive switching device, often realized as metal-isolator-metal systems. It has been shown that the calculated electric field and force distribution in case of the chosen example system Cu/a-SiO$_2$/Cu are in agreement with fundamental field theoretical expectations.

Future work on the basis of the proposed model for electric fields is planned. In particular, from a technical point of view an efficient and full implementation in LAMMPS is needed. From the physics point of view, we believe that an approximation for the Gaussian-type orbitals (GTOs) within the computation of the overlap integrals for the effective electronegativities should be realized, since GTOs are not needed for the computation of the respective Coulomb interactions.

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